

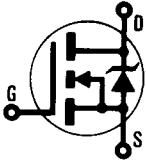
INTERNATIONAL RECTIFIER



AVALANCHE ENERGY RATED AND dv/dt RATED

HEXFET[®] TRANSISTOR

IRFM044



N-CHANNEL

60 Volt, 0.040 Ohm HEXFET

The HEXFET[®] technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies and virtually any application where military and/or high reliability is required.

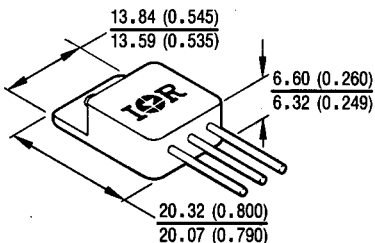
Product Summary

Part Number	BV_{DS}	$R_{DS(on)}$	I_D
IRFM044	60V	0.040 Ω	35A*

FEATURES:

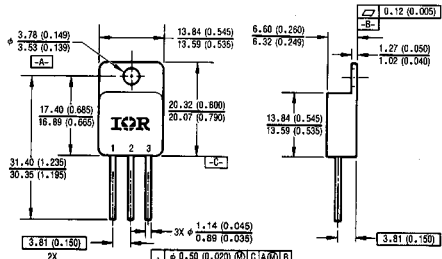
- Avalanche Energy Rating
- Isolated and Hermetically Sealed
- Alternative to TO-3 Package
- Simple Drive Requirements
- Ease of Paralleling
- Ceramic Eyelets

CASE STYLE AND DIMENSIONS



CAUTION

BERYLLIA WARNING PER MIL-S-19500
SEE PAGE I-276



LEGEND

- 1 DRAIN
- 2 SOURCE
- 3 GATE

NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M - 1982.
- 2 ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

Conforms to JEDEC Outline TO-254AA*

Dimensions in Millimeters and (Inches)

*For leadform configurations see page I-276, fig. 15

Absolute Maximum Ratings

Parameter	IRFM044	Units
I_D @ $V_{GS} = 10V$, $T_C = 25^\circ C$ Continuous Drain Current	35*	A
I_D @ $V_{GS} = 10V$, $T_C = 100^\circ C$ Continuous Drain Current	28	
I_{DM} Pulsed Drain Current ①	180	
P_D @ $T_C = 25^\circ C$ Max. Power Dissipation	125	W
	Linear Derating Factor	W/K ⑤
V_{GS} Gate-to-Source Voltage	± 20	V
E_{AS} Single Pulse Avalanche Energy ②	340	mJ
dv/dt Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J Operating Junction Temperature	-55 to 150	$^\circ C$
T_{STG} Storage Temperature Range		
	Lead Temperature 300 (0.063 in. (1.6 mm) from case for 10s)	
Weight	9.3 (typical)	g

* I_D current limited by pin diameterElectrical Characteristics @ $T_J = 25^\circ C$ (Unless Otherwise Specified)

Parameter		Min.	Typ.	Max.	Units	Test Conditions		
BV _{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V _{GS} = 0V, I _D = 1.0 mA		
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.68	—	V/°C	Reference to 25°C, I _D = 1.0 mA		
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.040	Ω	V _{GS} = 10V, I _D = 28A		
		—	—	0.050		V _{GS} = 10V, I _D = 35A ④		
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250 μA		
g _{fs}	Forward Transconductance	17	—	—	S (f)	V _{DS} ≥ 15V, I _{DS} = 28A ④		
I _{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V _{DS} = 0.8 × Max. Rating, V _{GS} = 0V		
		—	—	250		V _{DS} = 0.8 × Max. Rating V _{GS} = 0V, T _J = 125°C		
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V		
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100	nA	V _{GS} = -20V		
Q _g	Total Gate Charge	39	—	88	nC	V _{GS} = 10V, I _D = 35A		
Q _{gs}	Gate-to-Source Charge	6.7	—	15		V _{DS} = 0.5 × Max. Rating		
Q _{gd}	Gate-to-Drain ("Miller") Charge	18	—	52		See Fig. 6 and 14		
t _{d(on)}	Turn-On Delay Time	—	—	23	ns	V _{DD} = 30V, I _D = 35A, R _G = 9.1Ω		
t _r	Rise Time	—	—	130		See Fig. 11		
t _{d(off)}	Turn-Off Delay Time	—	—	81				
t _f	Fall Time	—	—	79				
L _D	Internal Drain Inductance	—	8.7	—	nH	Measured from the drain lead, 6 mm (0.25 in.) from package to center of die.	Modified MOSFET symbol showing the internal inductances. 	
L _S	Internal Source Inductance	—	8.7	—		Measured from the source lead, 6 mm (0.25 in.) from package to source bonding pad.		
C _{iss}	Input Capacitance	—	2400	—	pF	V _{GS} = 0V, V _{DS} = 25V		
C _{oss}	Output Capacitance	—	1100	—		f = 1.0 MHz		
C _{rss}	Reverse Transfer Capacitance	—	230	—		See Fig. 5		
C _{DC}	Drain-to-Case Capacitance	—	12	—				



Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S Continuous Source Current (Body Diode)	—	—	35*	A	Modified MOSFET symbol showing the integral Reverse p-n junction rectifier. 
I_{SM} Pulsed Source Current (Body Diode) ①	—	—	180		
V_{SD} Diode Forward Voltage	—	—	2.5		$T_J = 25^\circ\text{C}$, $I_S = 35\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr} Reverse Recovery Time	—	—	220	nS	$T_J = 25^\circ\text{C}$, $I_F = 35\text{A}$, $dI/dt \leq 100\text{ A}/\mu\text{s}$ ④
Q_{RR} Reverse Recovery Charge	—	—	1.6	μC	$V_{DD} \leq 50\text{V}$
t_{on} Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

* I_S current limited by pin diameter

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	1.0	K/W ⑤	
R_{thCS} Case-to-Sink	—	0.21	—		Mounting surface flat, smooth, and greased
R_{thJA} Junction-to-Ambient	—	—	48		Typical socket mount

① Repetitive Rating; Pulse width limited by maximum junction temperature (see figure 9) Refer to current HEXFET reliability report

② @ $V_{DD} = 25\text{V}$, Starting $T_J = 25^\circ\text{C}$, $L \geq 320\ \mu\text{H}$, $R_G = 25\Omega$, Peak $I_L = 35\text{A}$

③ $I_{SD} \leq 35\text{A}$, $dI/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ\text{C}$ Suggested $R_G = 9.1\Omega$

④ Pulse width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2\%$

⑤ $K/W = ^\circ\text{C}/\text{W}$
 $W/K = \text{W}/^\circ\text{C}$

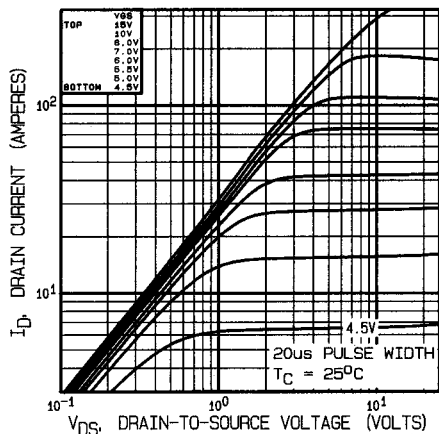
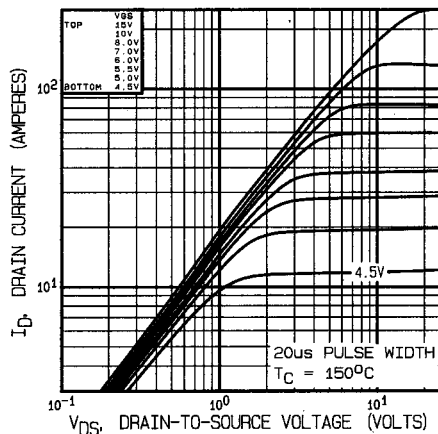
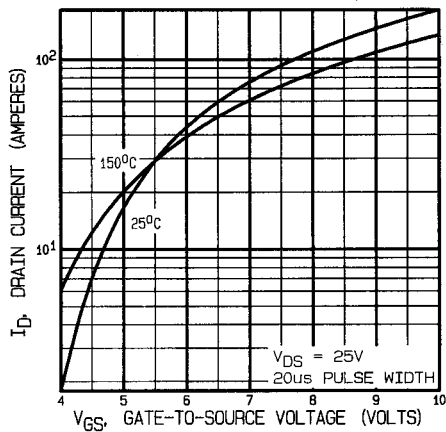
Fig. 1 — Typical Output Characteristics, $T_C = 25^\circ\text{C}$ Fig. 2 — Typical Output Characteristics, $T_C = 150^\circ\text{C}$ 

Fig. 3 — Typical Transfer Characteristics

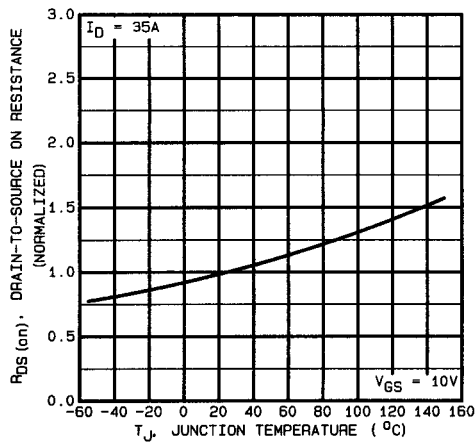
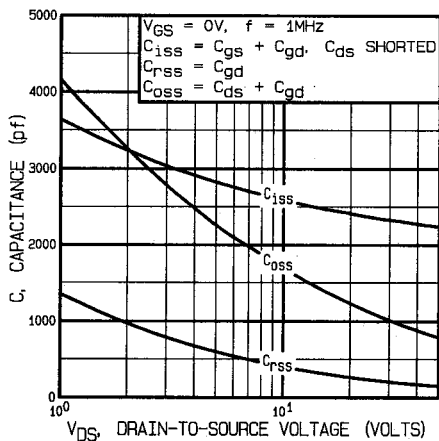
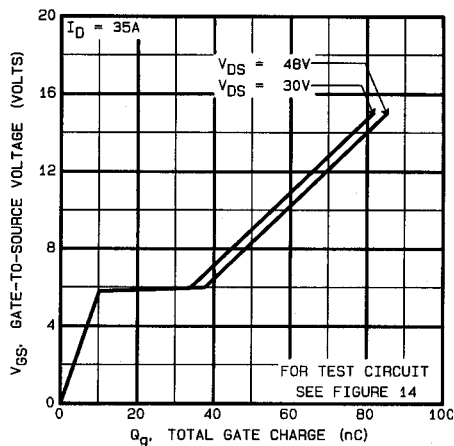
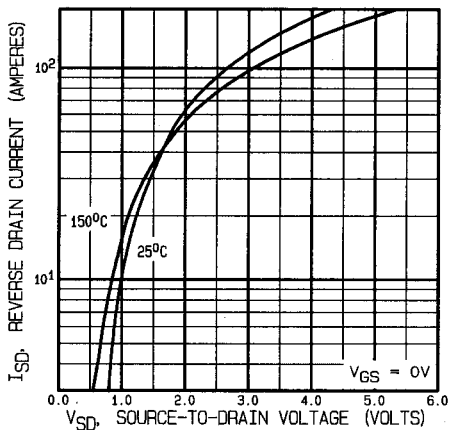
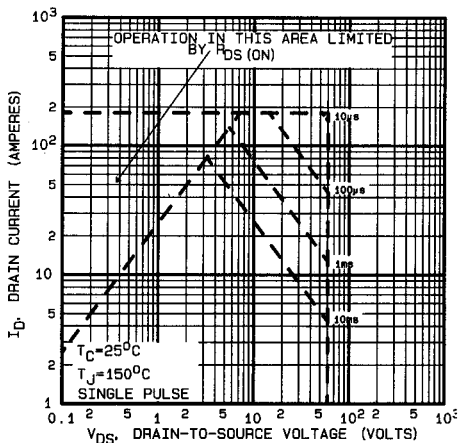


Fig. 4 — Normalized On-Resistance Vs. Temperature


Fig. 5 — Typical Capacitance Vs. Drain-to-Source Voltage

Fig. 6 — Typical Gate Charge Vs. Gate-to-Source Voltage

Fig. 7 — Typical Source-Drain Diode Forward Voltage

Fig. 8 — Maximum Safe Operating Area

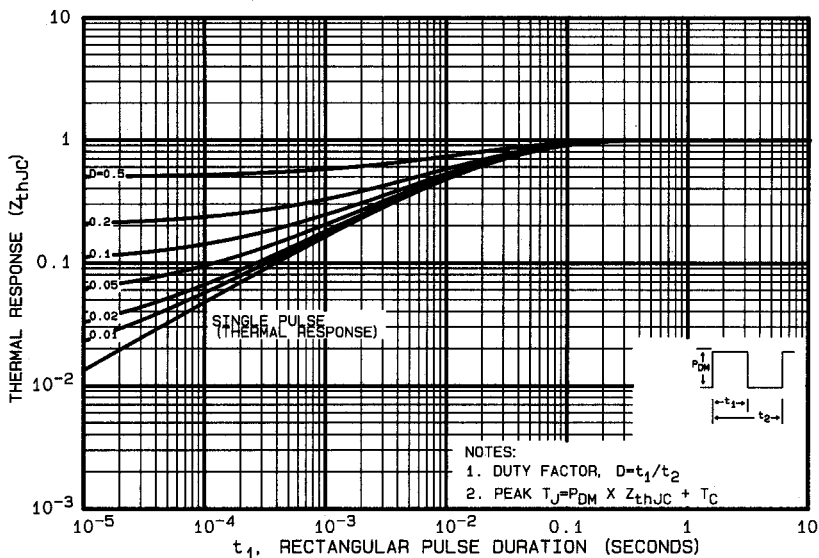


Fig. 9 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

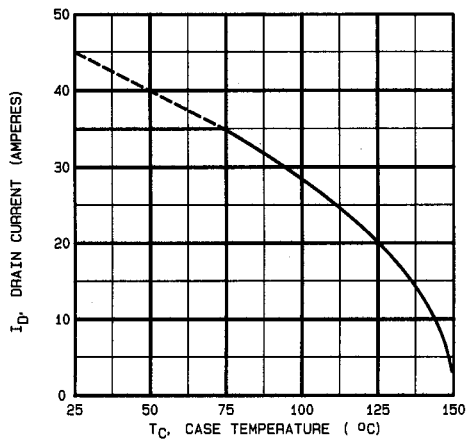


Fig. 10 — Maximum Drain Current Vs. Case Temperature

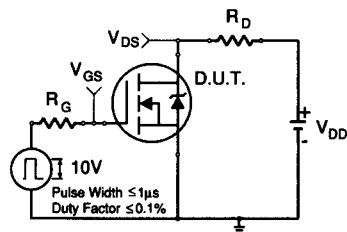


Fig. 11a — Switching Time Test Circuit

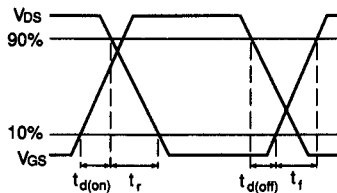
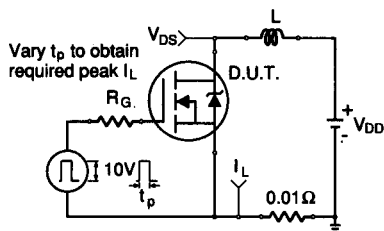
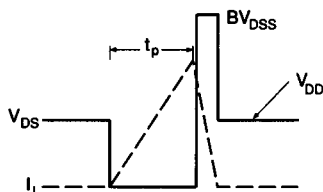
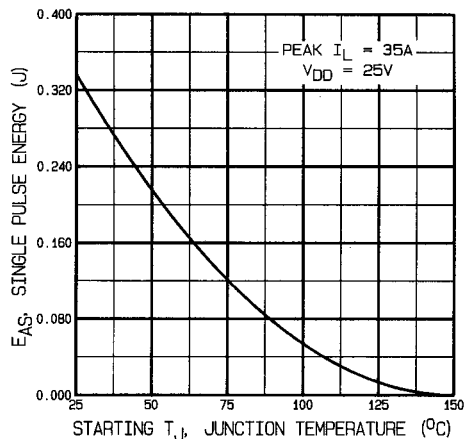
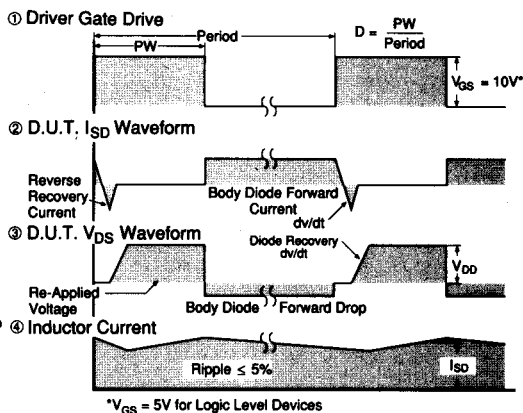
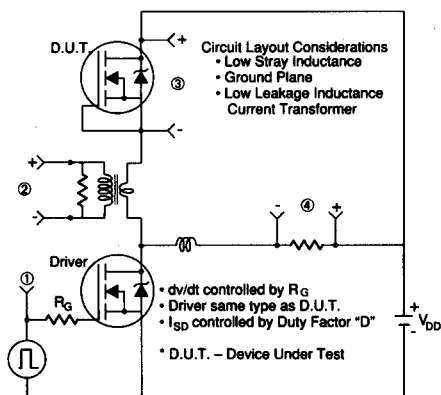


Fig. 11b — Switching Time Waveforms


Fig. 12a — Unclamped Inductive Test Circuit

Fig. 12b — Unclamped Inductive Waveforms

Fig. 12c — Maximum Avalanche Energy Vs. Starting Junction Temperature

Fig. 13 — Peak Diode Recovery dv/dt Test Circuit

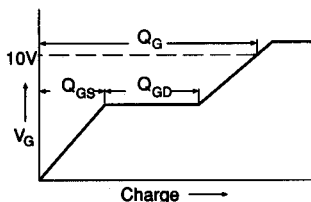


Fig. 14a — Basic Gate Charge Waveform

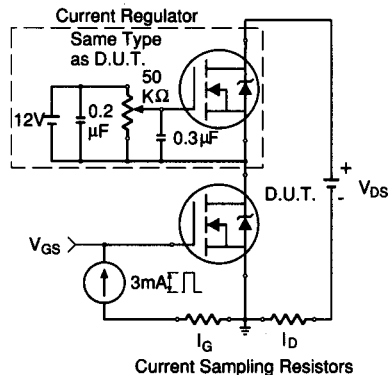


Fig. 14b — Gate Charge Test Circuit

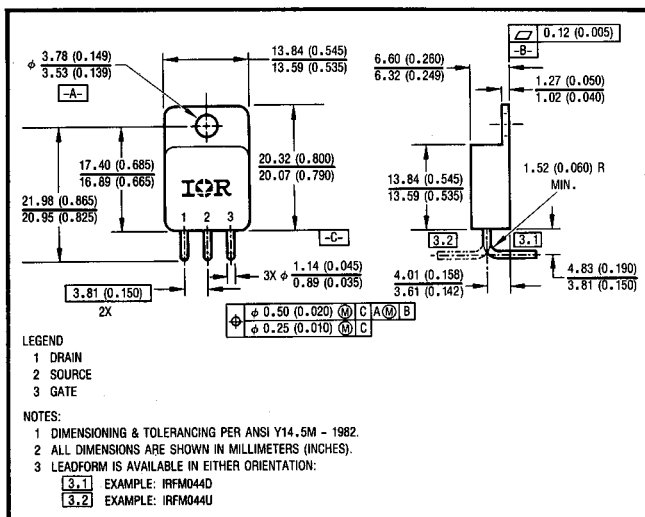


Fig. 15 — Optional Leadforms for Outline TO-254

BERYLLIA WARNING PER MIL-S-19500

Packages containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.